MSKSEMI















ESD

TVS

TSS

MOV

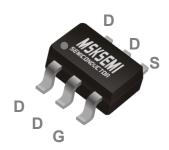
GDT

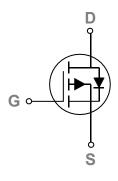
PLED

Broduct data sheet



SOT23-6 Pin Configuration





Features

- $-60V, -3.3A, RDS(ON) = 70 m\Omega@VGS = -10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Motor Drive
- Power Tools
- LED Lighting

BVDSS RDSON ID -60V $70m\Omega$ -3.3A

Absolute Maximum Ratings Tc=25°C unless otherwise noted

| Symbol | Parameter | Rating | Units |
|------------------|---|------------|-------|
| V _{DS} | Drain-Source Voltage | -60 | V |
| V _{GS} | Gate-Source Voltage | ±20 | V |
| | Drain Current – Continuous (T _A =25°C) | -3.3 | Α |
| ID | Drain Current – Continuous (T _A =70°C) | -2.6 | Α |
| Ірм | Drain Current – Pulsed ¹ | -13.2 | Α |
| D | Power Dissipation (T _A =25°C) | 2 | W |
| P_D | Power Dissipation – Derate above 25°C | 0.016 | W/°C |
| T _{STG} | Storage Temperature Range | -55 to 150 | °C |
| TJ | Operating Junction Temperature Range | -55 to 150 | °C |

Thermal Characteristics

| Symbol | Parameter | Тур. | Max. | Unit |
|--------|--|------|------|------|
| Reja | Thermal Resistance Junction to ambient | | 62.5 | °C/W |









Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Off Characteristics

| Symbol | Parameter | Conditions | | Тур. | Max. | Unit |
|-------------------|--------------------------------|---|-----|------|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V , I _D =-250uA | -60 | | | V |
| | Drain Source Lookage Current | V _{DS} =-60V , V _{GS} =0V , T _J =25°C | | | -1 | uA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =-48V , V _{GS} =0V , T _J =125°C | | | -10 | uA |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±20V , V _{DS} =0V | | | ±100 | nA |

On Characteristics

| D-2/200 | Static Drain-Source On-Resistance | V _{GS} =-10V , I _D =-2A | | 70 | 105 | mΩ |
|---------------------|-------------------------------------|---|------|------|------|----|
| R _{DS(ON)} | Static Dialii-Source Off-Nesistance | V _{GS} =-4.5V , I _D =-1A | | 80 | 130 | mΩ |
| V _{GS(th)} | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =-250uA | -1.0 | -1.6 | -2.5 | V |
| gfs | Forward Transconductance | V _{DS} =-10V , I _D =-1A | | 3 | | S |

Dynamic and switching Characteristics

| Qg | Total Gate Charge ^{3, 4} | | 10 | |
|---------------------|-------------------------------------|---|----------|----|
| Qgs | Gate-Source Charge ^{3, 4} | V _{DS} =-30V , V _{GS} =-10V , I _D =-1A | 1.6 | nC |
| Q_{gd} | Gate-Drain Charge ^{3, 4} | | 3 | |
| T _{d(on)} | Turn-On Delay Time ^{3, 4} | | 8 | |
| Tr | Rise Time ^{3, 4} | V_{DD} =-30 V , V_{GS} =-10 V , R_{G} =6 Ω | 15.4 | |
| T _{d(off)} | Turn-Off Delay Time ^{3, 4} | I _D =-1A | 42.8 | ns |
| Tf | Fall Time ^{3, 4} | | 8.4 | |
| Ciss | Input Capacitance | | 720 | |
| Coss | Output Capacitance | V_{DS} =-30V , V_{GS} =0V , F=1MHz | 42 | pF |
| Crss | Reverse Transfer Capacitance | | 32 | |
| R _g | Gate resistance | V _{GS} =0V, V _{DS} =0V, F=1MHz | 22 | Ω |

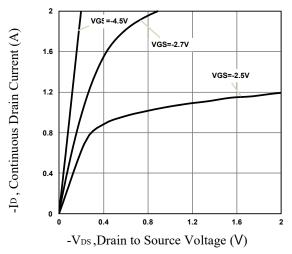
Drain-Source Diode Characteristics and Maximum Ratings

| Symbol | Parameter | Conditions | | Тур. | Max. | Unit |
|-----------------|---------------------------|--|--|------|------|------|
| Is | Continuous Source Current | V-=V-=0V Force Current | | | -3.3 | Α |
| Isм | Pulsed Source Current | V _G =V _D =0V , Force Current | | | -6.6 | Α |
| V _{SD} | Diode Forward Voltage | V _{GS} =0V , I _S =-1A , T _J =25°C | | | -1 | V |
| t _{rr} | Reverse Recovery Time | V _R =-50V, I _S =-1A | | 30 | | ns |
| Qrr | Reverse Recovery Charge | di/dt=100A/µs, Tյ=25°C | | 15 | | nC |

Note:

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- Kepetitive Kaling . F used width limited by maximum juricition temper
 V_{DD}=-25V,V_{GS}=-10V,L=0.1mH,I_{AS}=-18A.,R_G=25Ω,Starting T_J=25°C.
 The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
 Essentially independent of operating temperature.





Typical Output Characteristics

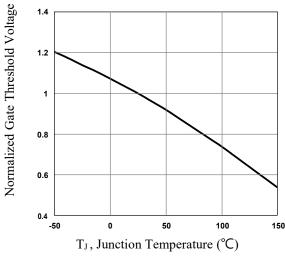


Fig.3 Normalized V_{th} vs. T_J

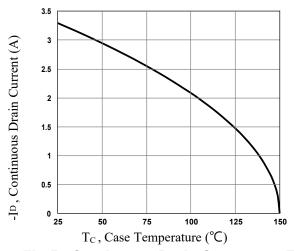


Fig.5 Continuous Drain Current vs. Tc

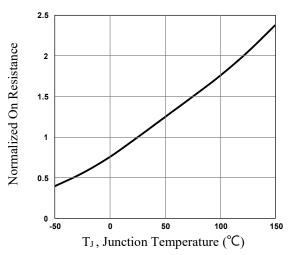


Fig.2 Normalized RDSON vs. TJ

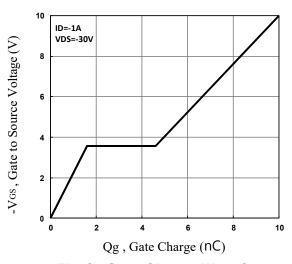


Fig.4 Gate Charge Waveform

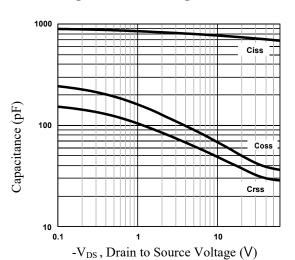


Fig.6 Capacitance Characteristics



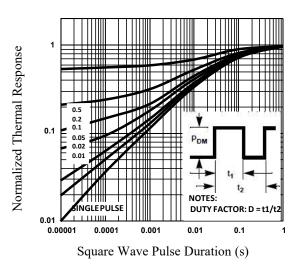


Fig.7 Normalized Transient Impedance

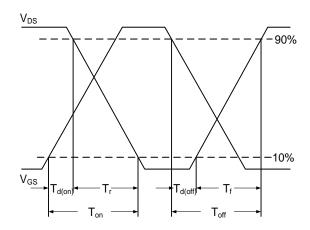


Fig.9 Switching Time Waveform

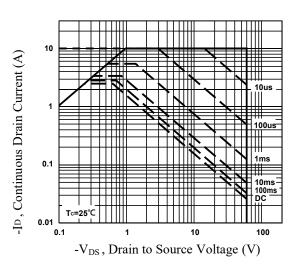
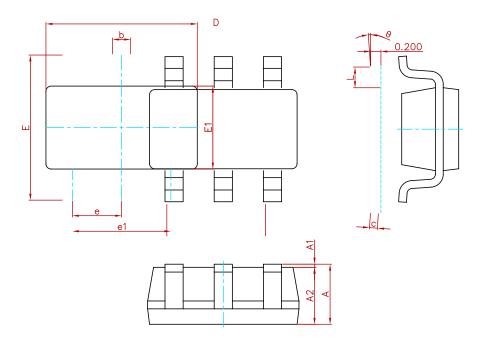


Fig.8 Maximum Safe Operation Area

FDC5614P HF

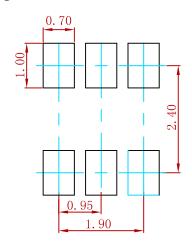


PACKAGE MECHANICAL DATA



| Symbol | Dimensions In | n Millimeters | Dimension | s In Inches |
|--------|---------------|---------------|-----------|-------------|
| Symbol | Min. | Max. | Min. | Max. |
| Α | 1.050 | 1.250 | 0.041 | 0.049 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| С | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 2.820 | 3.020 | 0.111 | 0.119 |
| E1 | 1.500 | 1.700 | 0.059 | 0.067 |
| Е | 2.650 | 2.950 | 0.104 | 0.116 |
| е | 0.950(| BSC) | 0.037 | (BSC) |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.300 | 0.600 | 0.012 | 0.024 |
| θ | 0° | 8° | 0° | 8° |

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

REEL SPECIFICATION

| P/N | PKG | QTY |
|----------|----------|------|
| FDC5614P | SOT-23-6 | 3000 |



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BSS340NWH6327XTSA1 MCM3400A-TP DMTH10H4M6SPS-13 IRF40SC240ARMA1 IPS60R1K0PFD7SAKMA1

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